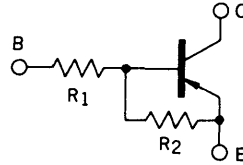


NEC

PNP SILICON TRANSISTOR AN1A4P

DESCRIPTION The AN1A4P is designed for use in medium speed switching circuit.

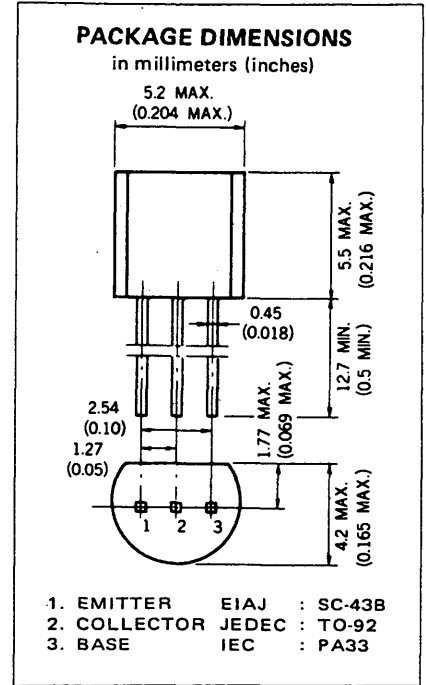
FEATURE • Bias resistors built-in type PNP transistor equivalent circuit.



$R_1 = 10\text{ k}\Omega$
 $R_2 = 47\text{ k}\Omega$

ABSOLUTE MAXIMUM RATINGS

Maximum Temperatures	
Storage Temperature	-55 to +150 °C
Junction Temperature	150 °C Maximum
Maximum Power Dissipation ($T_a = 25\text{ °C}$)	
Total Power Dissipation	300 mW
Maximum Voltages and Currents ($T_a = 25\text{ °C}$)	
V_{CBO} Collector to Base Voltage	-60 V
V_{CEO} Collector to Emitter Voltage	-50 V
V_{EBO} Emitter to Base Voltage	-5.0 V
$I_{C(DC)}$ Collector Current (DC)	-100 mA
$I_{C(pulse)}$ Collector Current (pulse)	-200 mA



ELECTRICAL CHARACTERISTICS ($T_a = 25\text{ °C}$)

SYMBOL	CHARACTERISTIC	MIN.	TYP.	MAX.	UNIT	TEST CONDITIONS
R_1	Input Resistance	7.0	10.0	13.0	$\text{k}\Omega$	
R_2	Input Resistance	32.9	47.0	61.1	$\text{k}\Omega$	
V_{IL}	Low Level Input Voltage		-0.68	-0.5	V	$V_{CE} = -5.0\text{ V}, I_C = -100\text{ }\mu\text{A}$
V_{IH}	Hi Level Input Voltage	-3.0	-1.0		V	$V_{CE} = -0.2\text{ V}, I_C = -5.0\text{ mA}$
t_{on}	Turn On Time		0.08	0.2	μs	$V_{CC} = -5.0\text{ V}, R_L = 1.0\text{ k}\Omega,$ $V_{in} = -5.0\text{ V},$ $PW = 2\text{ }\mu\text{s}, \text{Duty Cycle} \leq 2\%$
t_{stg}	Storage Time		1.5	5.0	μs	
t_{off}	Turn Off Time		1.8	6.0	μs	
h_{FE1}	DC Current Gain	85	140	340	-	$V_{CE} = -5.0\text{ V}, I_C = -5.0\text{ mA}$
h_{FE2}	DC Current Gain	95	190		-	$V_{CE} = -5.0\text{ V}, I_C = -5.0\text{ mA}$
$V_{CE(sat)}$	Collector Saturation Voltage		-0.04	-0.2	V	$I_C = -5.0\text{ mA}, I_B = -0.25\text{ mA}$
I_{CBO}	Collector Cutoff Current			-0.1	μA	$V_{CB} = -50\text{ V}, I_E = 0$

TYPICAL CHARACTERISTICS ($T_a = 25^\circ\text{C}$)

